

METHOD OF FABRICATING A SEMICONDUCTOR DEVICE

FIELD OF THE INVENTION

The present invention relates to the field of semiconductors and, more particularly, to an improved dielectric for increasing semiconductor performance.

CROSS-REFERENCES TO RELATED APPLICATIONS

This application is a divisional of U.S. Patent Application Serial No. 10/273,667 filed October 18, 2002, ^{now PAT 6,670,231} which is a divisional of U.S. Patent Application Serial No. 09/653,096, filed August 31, 2000, ^{now PAT 6,576,964}.

Dle This application is related to commonly assigned U.S. Patent Application Serial Nos.: 09/653,639, ^{now PAT 6,410,968} METHOD FOR FORMING A BARRIER LAYER TO INCREASE SEMICONDUCTOR DEVICE PERFORMANCE, filed August 31, 2000, by Powell et al. and 09/653,298, ^{now PAT 6,521,544} METHOD FOR FORMING A DIELECTRIC LAYER AT A LOW TEMPERATURE, filed August 31, 2000, by Mercaldi et al., the disclosures of which are incorporated herein by reference.